IN THE SPECIFICATION:

The specification as amended below with replacement paragraphs shows added text with underlining and deleted text with ~~strikethrough~~.

Please REPLACE paragraphs [0014] and [0015] on page 4 with the following amended paragraphs:

[0014] To achieve the foregoing and/or other aspects, the present invention provides an organic electroluminescent device comprising a substrate; a first electrode to define a pixel region on the substrate; multiple organic film layers for light emission on the first electrode; and a second electrode formed on the multiple organic film layers, wherein the multiple organic film layers comprise at least an emitting layer, a hole injection layer and/or a hole ~~transfer~~ transport layer, and the hole injection layer and/or the hole ~~transfer~~ transport layer comprise or comprises an electron acceptor material.

[0015] Furthermore, the present invention provides an organic electroluminescent device comprising a substrate; a first electrode to define a pixel region on the substrate; multiple organic film layers for light emission on the first electrode; and a second electrode formed on the multiple organic film layers, wherein the multiple organic film layers comprise at least an emitting layer, a hole-blocking layer, an electron injection layer and/or an electron ~~transfer~~ transport layer, and the hole-blocking layer, the electron injection layer and/or the electron ~~transfer~~ transport layer comprise an electron donor material.

Please REPLACE paragraph [0024] on page 6 with the following amended paragraph:

[0024] In an organic electroluminescent device according to an embodiment of the present invention, as shown in FIG. 3, numeral 300 (not to scale), a first electrode 312 to define a pixel region is first formed on a semiconductor substrate 314 such as polysilicon, and then multiple organic film layers comprising at least an emitting layer 308, a hole injection layer and/or a hole ~~transfer~~ transport layer 310 are formed on the first electrode 312. The multiple organic film layers are layers that may be used as a common layer, regardless of patterning of the emitting

layer, wherein the hole injection layer and/or the hole ~~transfer~~ transport layer 310 include(s) an electron acceptor material. Therefore, an organic electroluminescent device of the present invention not only obtains a luminance quenching effect and device stability, but also suppresses or reduces an increase of the driving voltage of the device.

Please REPLACE paragraphs [0026] and [0027] on page 6 with the following amended paragraphs:

[0026] 0.01 to 10 wt.% of the electron acceptor material is generally used for the total weight of the hole injection layer and/or the hole ~~transfer~~ transport layer.

[0027] The hole injection layer and/or the hole ~~transfer~~ transport layer may be formed in a thin film by, for example, co-deposition or spin-coating.

Please REPLACE paragraph [0032] on page 7 with the following amended paragraph:

[0032] Furthermore, a deposition thickness of the hole injection layer and/or the hole ~~transfer~~ transport layer is generally 1 to 4,000 Å, and an ordinarily used emitting material, regardless of whether it is a high molecular weight material or a low molecular weight material, may be used as the emitting layer.

Please REPLACE paragraphs [0034] and [0035] on page 7 with the following amended paragraphs:

[0034] On the other hand, in another embodiment of the present invention, the multiple organic film layers comprise at least an emitting layer, a hole-blocking layer and/or an electron ~~transfer~~ transport layer, and the hole-blocking layer and/or the electron ~~transfer~~ transport layer comprises an electron donor material. An emitting layer is first formed on the first electrode to

define a pixel region in this embodiment. The hole-blocking layer and/or the electron ~~transfer~~ transport layer are formed on the emitting layer which is on the substrate.

[0035] An electron donor material is included in the hole-blocking layer and/or the electron ~~transfer~~ transport layer.

Please REPLACE paragraph [0037] on page 8 with the following amended paragraph:

[0037] On the other hand, the hole-blocking layer and/or the electron ~~transfer~~ transport layer are formed in a thickness of 1 to 4,000 Å and may form a thin film by, for example, co-deposition or spin coating.

Please REPLACE paragraph [0045] on page 9 with the following amended paragraph:

[0045] When forming a high molecular weight organic electroluminescent device, an ITO substrate is prepared by UV/O_3 treating the cleaned substrate after cleaning a substrate in isopropyl alcohol (IPA) and acetone. In the case of the high molecular weight organic EL device, after PEDOT or PANI is coated on the whole substrate, ~~PEDTO~~ PEDOT or PANI is wiped on a cathode contact part, which is used as a hole injection layer on the ITO substrate to a thickness of hundreds of Å and heat-treating the PEDOT or PANI coated ITO substrate at a temperature of 200°C for 5 minutes. After a solution is coated on the whole substrate, the solution is once more wiped on the cathode contact part, which is prepared by blending the HTL material with an electron acceptor material on an HIL to a thickness of hundreds of Å and heat-treating the blended solution coated HIL at a temperature of 200°C for 5 minutes. R, G and B materials are patterned on the HTL using laser induced thermal imaging (LITI).

Please REPLACE paragraph [0052] on page 10 with the following amended paragraph:

[0052] A hole injection layer (HIL formed of PEDOT/PSS manufactured by BAYER CORPORATION) was coated on the UV/O_3 treated ITO substrate to a thickness of 0, 60, 80 and 120 nm under appropriate spin coating speed conditions after cleaning an ITO substrate prepared by patterning ITO on a substrate and UV/O_3 treating the cleaned ITO substrate for 15 minutes. HTL on a cathode contact part of the hole injection layer coated substrate was peeled off, and test cells on which HIL was coated were moved into a ~~globe~~ glove box so that the test cells were dried at a temperature of 200°C for 5 minutes.